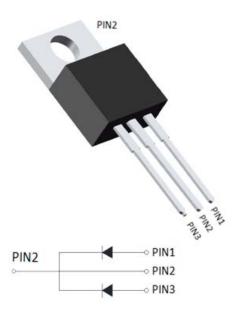




Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

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PARAMETER	SYMBOL	UNIT	MBR3060CT		
Device marking code			MBR3060CT		
Repetitive Peak Reverse Voltage	VRRM	V	60		
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	lO	Α	30		
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave,1 cycle, T _a =25℃	IFSM	Α	250		
Current Squared Time @1ms≤t≤8.3ms Tj=25℃,	l ² t	A ² s	260		
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ + 150		
Junction Temperature Tj		$^{\circ}$ C	-55 ~ +150		

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

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PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR3060CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.72
Maximum DC reverse current at rated DC blocking voltage perdiode	IRRM1	mA ·	VRM=VRRM T _a =25℃	0.2
	IRRM2		VRM=VRRM T _a =125°C	50

MBR3060CT

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL	UNIT	MBR3060CT
Thermal Resistance	Between junction and case	R _{θJ-C}	°C/W	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR3060CT	Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

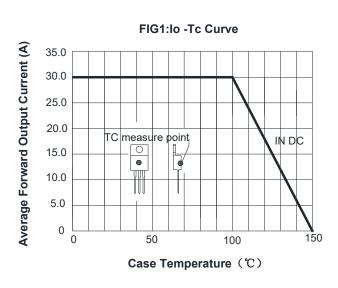
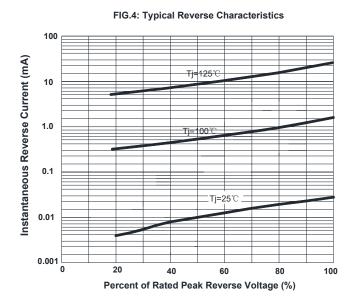


FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 2 5 10 50 100 **Number of Cycles**

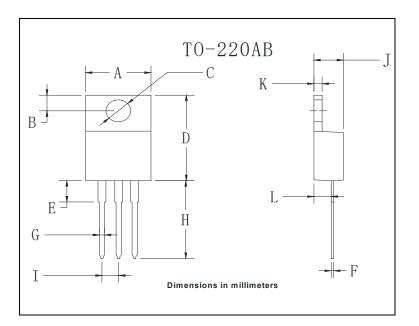
FIG3: Forward Voltage 100 60 Instantaneous Forward Current (A) 20 10 5.0 1.0 0.5 0.2 Ta=25℃ 0.1 0 0.6 0.7 0.8 0.4 0.5 Instantaneous Forward Voltage (V)







■Outline Dimensions



TO-220AB				
Dim	Min	Max		
Α	9.5	10.9		
В	2.22	3.27		
С	3.34	4.31		
D	14.5	15.5		
Е	3.16	4.46		
F	0.28	0.64		
G	0.68	0.94		
Н	13.06	14.62		
I	2.01	3.07		
J	4.04	5.1		
K	1.14	1.4		
L	2.14	3.19		



MBR3060CT

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